

2N4401 / MMBT4401 NPN General-Purpose Amplifier

Description

This device is designed for use as a medium power amplifier and switch requiring collector currents up to 500 mA.



Figure 1. 2N4401 Device Package

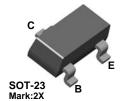


Figure 2. MMBT4401 Device Package

Ordering Information

Part Number	Marking	Package	Packing Method
2N4401BU	2N4401	TO-92 3L	Bulk
2N4401TF	2N4401	TO-92 3L	Tape and Reel
2N4401TFR	2N4401	TO-92 3L	Tape and Reel
2N4401TA	2N4401	TO-92 3L	Ammo
2N4401TAR	2N4401	TO-92 3L	Ammo
MMBT4401	2X	SOT-23 3L	Tape and Reel

Absolute Maximum Ratings(1),(2)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^{\circ}\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
V _{CEO}	Collector-Emitter Voltage	40	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	6.0	V
I _C	Collector Current - Continuous	600	mA
T _{J,} T _{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Notes:

- 1. These ratings are based on a maximum junction temperature of 150°C.
- 2. These are steady-state limits. ON Semiconductor should be consulted on applications involving pulsed or low-duty cycle operations.

Thermal Characteristics

Values are at $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter	Ma	Unit	
	Farameter	2N4401 ⁽³⁾	MMBT4401 ⁽⁴⁾	Uill
P _D	Total Device Dissipation	625	350	mW
	Derate Above 25°C	5.0	2.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

Notes:

- 3. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.
- 4. Device mounted on FR-4 PCB 1.6 inch x 1.6 inch x 0.06 inch.

Electrical Characteristics

Values are at $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Max.	Unit
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage ⁽⁵⁾	I _C = 1.0 mA, I _B = 0	40		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 0.1 mA, I _E = 0	60		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 0.1 \text{ mA}, I_C = 0$	6.0		V
I _{BL}	Base Cut-Off Current	$V_{CE} = 35 \text{ V}, V_{EB} = 0.4 \text{ V}$		0.1	μΑ
I _{CEX}	Collector Cut-Off Current	$V_{CE} = 35 \text{ V}, V_{EB} = 0.4 \text{ V}$		0.1	μΑ
		$I_C = 0.1 \text{ mA}, V_{CE} = 1.0 \text{ V}$	20		
		$I_C = 1.0 \text{ mA}, V_{CE} = 1.0 \text{ V}$	40		
h _{FE}	DC Current Gain ⁽⁵⁾	$I_C = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$	80		
		$I_C = 150 \text{ mA}, V_{CE} = 1.0 \text{ V}$	100	300	
		$I_C = 500 \text{ mA}, V_{CE} = 2.0 \text{ V}$	40		
\/ (oot)	Collector-Emitter Saturation	I _C = 150 mA, I _B = 15 mA		0.40	V
V _{CE} (sat)	Voltage ⁽⁵⁾	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.75	7 v
\/ (oot)	Dana Fasittan Oatsantian Vallaga (5)	I _C = 150 mA, I _B = 15 mA	0.75	0.95	V
V _{BE} (sat)	Base-Emitter Saturation Voltage ⁽⁵⁾	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		1.20	7 v
f _T	Current Gain - Bandwidth Product	I _C = 20 mA, V _{CE} = 10 V, f = 100 MHz	250		MHz
C _{cb}	Collector-Base Capacitance	$V_{CB} = 5.0 \text{ V}, I_{E} = 0,$ f = 140 kHz		6.5	pF
C _{eb}	Emitter-Base Capacitance	$V_{BE} = 0.5 \text{ V}, I_{C} = 0,$ f = 140 kHz		30	pF
h _{ie}	Input Impedance	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 1.0 kHz	1.0	15.0	kΩ
h _{re}	Voltage Feedback Ratio	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 1.0 kHz	0.1	8.0	x10 ⁻⁴
h _{fe}	Small-Signal Current Gain	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 1.0 kHz	40	500	
h _{oe}	Output Admittance	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 1.0 kHz	1.0	30	μmhos
t _d	Delay Time	V _{CC} = 30 V, V _{EB} = 2 V,		15	ns
t _r	Rise Time	$I_C = 150 \text{ mA}, I_{B1} = 15 \text{ mA}$		20	ns
t _s	Storage Time	$V_{CC} = 30 \text{ V}, I_{C} = 150 \text{ mA},$		225	ns
t _f	Fall Time	I _{B1} = I _{B2} = 15 mA		30	ns

Note:

5. Pulse test: pulse width $\leq 300~\mu s,$ duty cycle $\leq 2.0\%.$

Typical Performance Characteristics

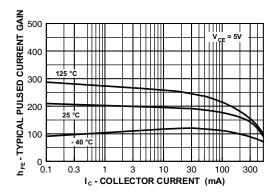


Figure 3. Typical Pulsed Current Gain vs. Collector Current

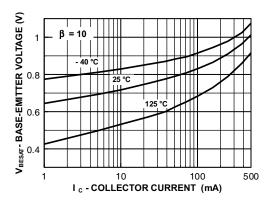


Figure 5. Base-Emitter Saturation Voltage vs. Collector Current

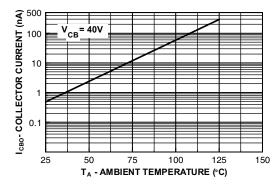


Figure 7. Collector Cut-Off Current vs. Ambient Temperature

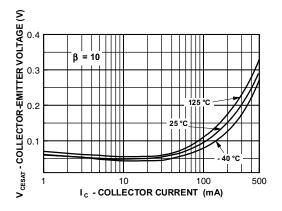


Figure 4. Collector-Emitter Saturation Voltage vs. Collector Current

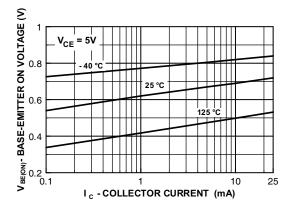


Figure 6. Base-Emitter On Voltage vs. Collector Current

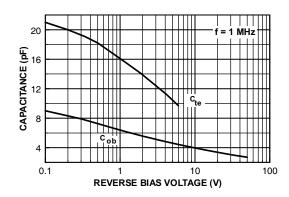


Figure 8. Emitter Transition and Output Capacitance vs. Reverse Bias Voltage

Typical Performance Characteristics (Continued)

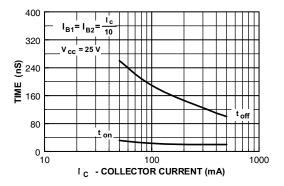


Figure 9. Turn-On and Turn-Off Times vs. Collector Current

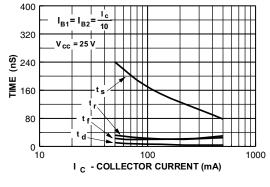


Figure 10. Switching Times vs.Collector Current

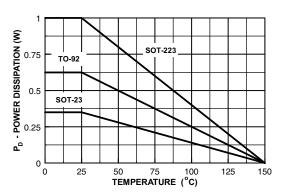


Figure 11. Power Dissipation vs. Ambient Temperature

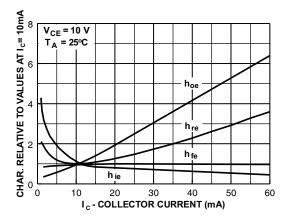


Figure 12. Common Emitter Characteristics

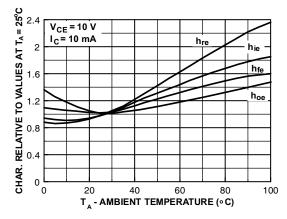


Figure 13. Common Emitter Characteristics

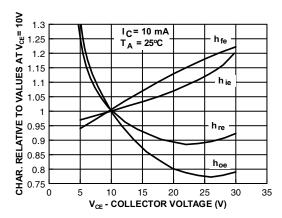


Figure 14. Common Emitter Characteristics

Physical Dimensions

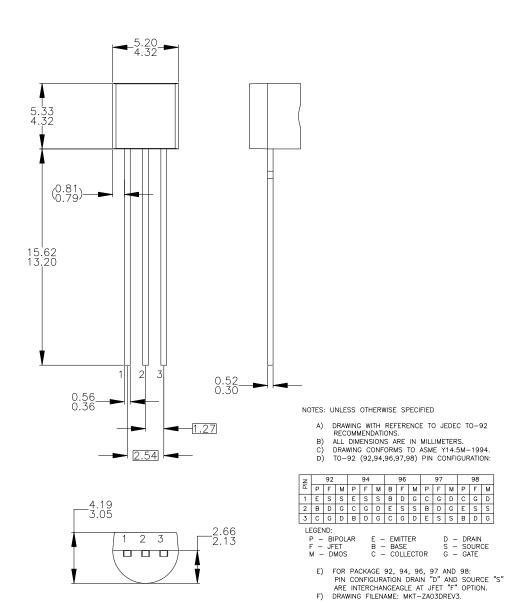
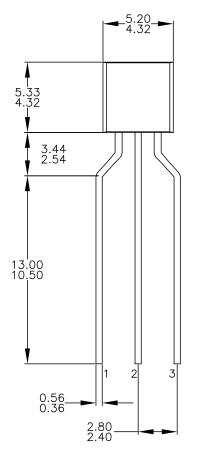
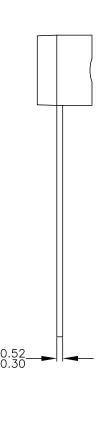
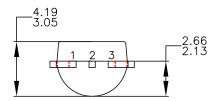


Figure 15. 3-Lead, TO-92, JEDEC TO-92 Compliant Straight Lead Configuration, Bulk Type

Physical Dimensions (Continued)







NOTES: UNLESS OTHERWISE SPECIFIED

- DRAWING CONFORMS TO JEDEC MS-013, VARIATION AC. ALL DIMENSIONS ARE IN MILLIMETERS. DRAWING CONFORMS TO ASME Y14.5M-2009. DRAWING FILENAME: MKT-ZA03FREV3. ON SEMICONDUCTOR

Figure 16. 3-Lead, TO-92, Molded, 0.2 In Line Spacing Lead Form, Ammo, Tape and Reel Type

Physical Dimensions (Continued) 0.95 2.92±0.20 3 1.40 1.30+0.20 2.20 2 0.60 0.37 (0.29) -0.95 ⊕ 0.20 M A B 1.00 1.90 1.90 LAND PATTERN RECOMMENDATION SEE DETAIL A 1.20 MAX 0.10 (0.93)0.10M C С 2.40±0.30 NOTES: UNLESS OTHERWISE SPECIFIED **GAGE PLANE** A) REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE H. 0.23 B) ALL DIMENSIONS ARE IN MILLIMETERS. C) DIMENSIONS ARE INCLUSIVE OF BURRS, 0.25 MOLD FLASH AND TIE BAR EXTRUSIONS. D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M - 1994. 0.20 MIN E) DRAWING FILE NAME: MA03DREV10 SEATING **PLANE** (0.55)DETAIL A

Figure 17. 3-LEAD, SOT23, JEDEC TO-236, LOW PROFILE

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